What is claimed is:

1. A liquid crystal display device comprising:

a pixel electrode at a pixel area between a gate line and a data line;

a switching device at an intersection between the gate line and the data line, the switching device comprising a light-shielding member overlapping the switching device and extending from an end at the pixel electrode side of a metal thin film provided within the switching device into the pixel area, for blocking light incident on the metal thin film.

2. The liquid crystal display device of claim 1, wherein the light-shielding member is at a front substrate opposed to a rear substrate, the rear substrate including the switching device and the pixel electrode.

3. The liquid crystal display device of claim 2, wherein the light-shielding member is a black matrix.

4. The liquid crystal display device of claim 1, wherein the switching device is a thin film transistor at the intersection between the gate line and the data line for driving the pixel electrode; and

wherein the metal thin film of the switching device is a drain electrode connected to the pixel electrode.

5. A liquid crystal display device comprising:

a pixel electrode at a pixel area between a gate line and a data line;

a charging device on the gate line, the charging device comprising:

a metal thin film;

a light-shielding member overlapping the charging device and extending from an end at the pixel electrode side of a metal thin film into the pixel area, for blocking light incident on the metal thin film.

6. The liquid crystal display device of claim 5, wherein the light-shielding member is formed at a front substrate opposed to a rear substrate that includes the charging device and the pixel electrode.

7. The liquid crystal display device of claim 6, wherein the light-shielding member is a black matrix.

8. The liquid crystal display device of claim 5, wherein the charging device is a storage capacitor including:

an upper electrode formed with the gate line; and

a dielectric layer between the upper electrode and the gate line,

wherein the metal thin film serves as the upper electrode.

9. A liquid crystal display device comprising:

a pixel electrode at a pixel area between a gate line and a data line;

a thin film transistor at an intersection between the gate line and the data line and including a first metal thin film;

a storage capacitor on the gate line and including a second metal thin film;

a black matrix at a boundary portion between pixel areas;

a first dummy black matrix connected to the black matrix and extending from an end at the pixel electrode side of the metal thin film into the pixel area; and

a second dummy black matrix connected to the black matrix and extending from an end at the pixel electrode side of the second metal thin film into the pixel area.

10. The liquid crystal display device of claim 9,

wherein the first metal thin film is a drain electrode connected to the pixel electrode, and

wherein the second metal thin film is an upper electrode between the gate line and a dielectric layer.

11. A method of fabricating a liquid crystal display device comprising the steps of:

forming a pixel electrode at a pixel area between a gate line and a data line;

forming a switching device including a metal thin film at an intersection between the gate line and the data line; and

forming a light-shielding member for blocking light incident on the metal thin film to overlap with the switching device, the light-shielding member extending from an end at the pixel electrode side of a metal thin film of the switching device into the pixel area.

12. The method of claim 11, wherein the switching device and the pixel electrode are formed on a rear substrate; and

wherein the light-shielding member is formed on a front substrate opposed to the rear substrate, with a liquid crystal layer therebetween.

13. The method of claim 12, wherein the light-shielding member is a black matrix.

14. The method of claim 12, wherein the switching device is a thin film transistor at the intersection between the gate line and the data line for driving the pixel electrode; and

wherein the metal thin film of the switching device is a drain electrode connected to the pixel electrode.

15. A method of fabricating a liquid crystal display device comprising the steps of:

forming a pixel electrode at a pixel area between a gate line and a data line;

forming a charging device including a first metal thin film on the gate line; and

forming a light-shielding member for blocking light incident on the metal thin film to overlap the metal thin film, the light-shielding member extending from an end at the pixel electrode side of the first metal thin film into the pixel area.

16. The method of claim 15, wherein the charging device and the pixel electrode are formed at a rear substrate; and

wherein the light-shielding member is formed at a front substrate opposed to the rear substrate with a liquid crystal layer therebetween.

17. The method of claim 16, wherein the light-shielding member is a black matrix.

18. The method of claim 15, wherein the first metal thin film is an upper electrode over the gate line and a dielectric layer.

19. A method of fabricating a liquid crystal display device comprising the steps of:

forming a pixel electrode at a pixel area between a gate line and a data line on a rear substrate;

forming a thin film transistor including a first metal thin film at an intersection between the gate line and the data line on the rear substrate;

forming a storage capacitor including a second metal thin film on the rear substrate and overlapping the gate line;

forming a black matrix on a front substrate opposed to the rear substrate at a boundary portion between pixel areas;

forming a first dummy black matrix extending from an end at the pixel electrode side of the first metal thin film into the pixel area on the front substrate; and

forming a second dummy black matrix extending from an end at the pixel electrode side of the second metal thin film into the pixel area on the front substrate.

20. The method of claim 19, wherein the metal thin film of the thin film transistor is a drain electrode connected to the pixel electrode; and

wherein the second metal thin film is an upper electrode between the gate line and a dielectric layer.